

单 P 沟道 MOSFET

ELM53435WA-S

<http://www.elm-tech.com>

■概要

ELM53435WA-S 是 P 沟道低输入电容，低工作电压，低导通电阻的大电流 MOSFET。另外，此芯片还内藏 ESD 保护电路。

■特点

- $V_{ds} = -200V$
- $I_d = -1.0A$
- $R_{ds(on)} = 2400m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} = 2600m\Omega$ ($V_{gs} = -4.5V$)
- 内藏 ESD 保护电路

■绝对最大额定值

如没有特别注明时, $T_a = 25^\circ C$

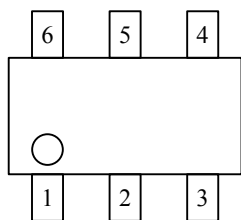
项目	记号	规格范围	单位	
漏极 - 源极电压	V_{ds}	-200	V	
栅极 - 源极电压	V_{gs}	± 20	V	
漏极电流 (定常) $T_j = 150^\circ C$	Id	$T_a = 25^\circ C$	-1.0	A
		$T_a = 70^\circ C$	-0.6	
漏极电流 (脉冲)	I_{dm}	-1.6	A	
容许功耗	Pd	$T_c = 25^\circ C$	3.2	W
		$T_c = 70^\circ C$	2.1	
动作结合部温度	T_j	150	$^\circ C$	
保存温度范围	T_{stg}	-55 ~ 150	$^\circ C$	

■热特性

项目	记号	典型值	最大值	单位
最大结合部 - 环境热阻	$R_{\theta ja}$		120	$^\circ C/W$

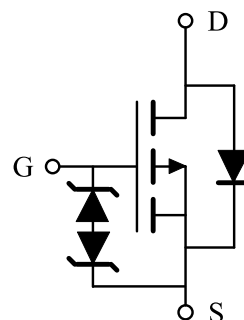
■引脚配置图

SOT-26(俯视图)



引脚编号	引脚名称
1	DRAIN
2	DRAIN
3	GATE
4	SOURCE
5	DRAIN
6	DRAIN

■电路图



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■电特性

如没有特别注明时, Ta=25℃

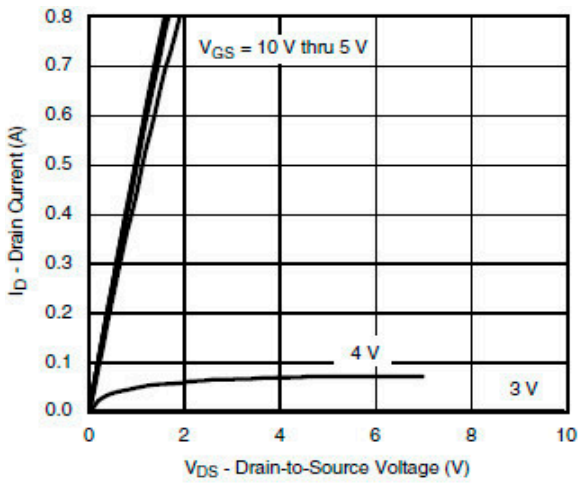
项目	记号	条件	最小值	典型值	最大值	单位
静态特性						
漏极 - 源极击穿电压	BV _{dss}	Id=-250μA, Vgs=0V	-200			V
栅极接地时漏极电流	Id _{ss}	Vds=-160V, Vgs=0V Ta=85℃			-1	μA
					-30	
栅极漏电流	Ig _{ss}	Vds=0V, Vgs=±20V			±10	μA
栅极阈值电压	Vgs(th)	Vds=Vgs, Id=-250μA	-1.0		-2.5	V
导通时漏极电流	Id(on)	Vgs=-10V, Vds≥-10V	-0.6			A
漏极 - 源极导通电阻	Rds(on)	Vgs=-10V, Id=-1.0A Vgs=-4.5V, Id=-0.6A		2000	2400	mΩ
				2100	2600	
正向跨导	Gfs	Vds=-10V, Id=-0.5A		1.5		S
二极管正向压降	Vsd	Is=-0.3A, Vgs=0V		-0.75	-1.20	V
寄生二极管最大连续电流	Is				-1.6	A
动态特性						
输入电容	Ciss	Vgs=0V, Vds=-75V, f=1MHz		155		pF
输出电容	Coss			8		pF
反馈电容	Crss			6		pF
开关特性						
总栅极电荷	Qg	Vgs=-10V, Vds=-75V Id≡-0.5A		4.20	8.00	nC
栅极 - 源极电荷	Qgs			0.98		nC
栅极 - 漏极电荷	Qgd			1.32		nC
导通延迟时间	td(on)	Vgs=-10V, Vds=-75V RL=75Ω, Id≡-1.0A Rgen=1.0Ω		5	10	ns
导通上升时间	tr			10	20	ns
关闭延迟时间	td(off)			20	40	ns
关闭下降时间	tf			10	20	ns

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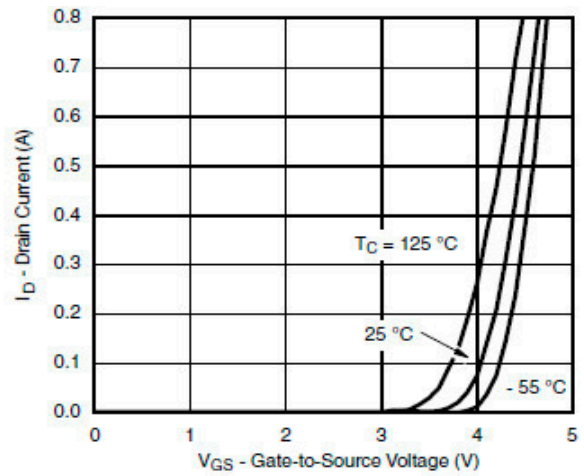
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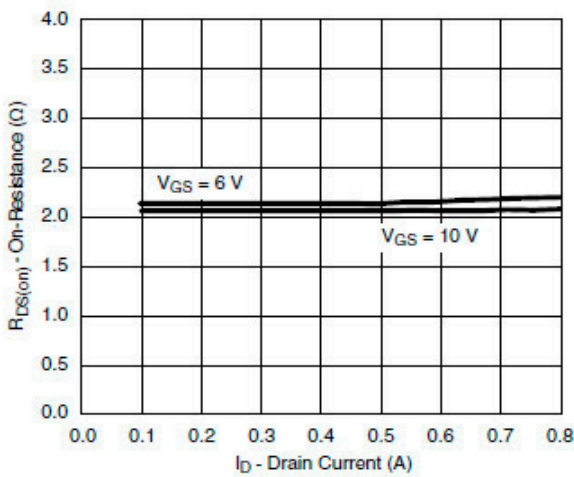
■ 标准特性和热特性曲线



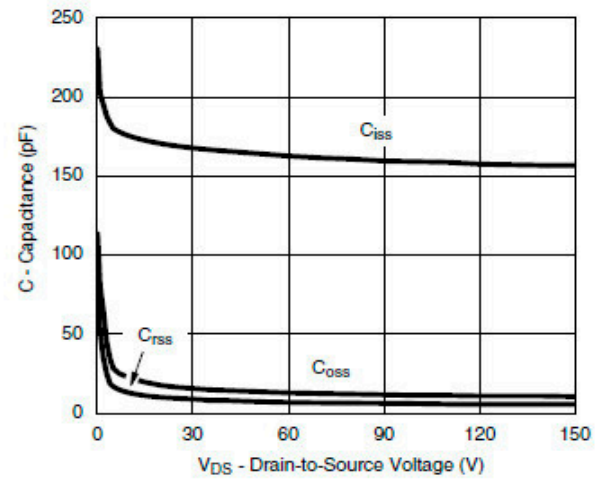
Output Characteristics



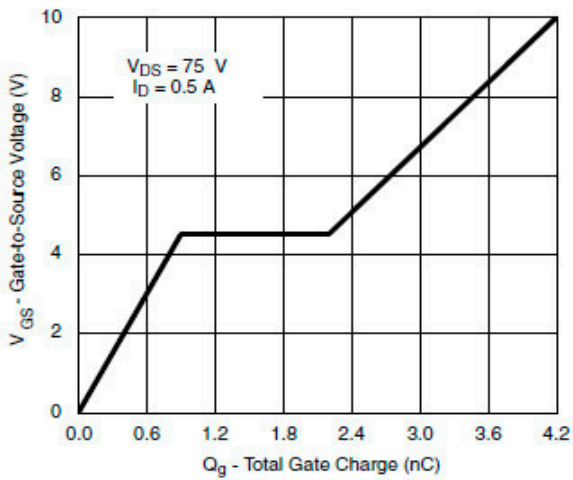
Transfer Characteristics



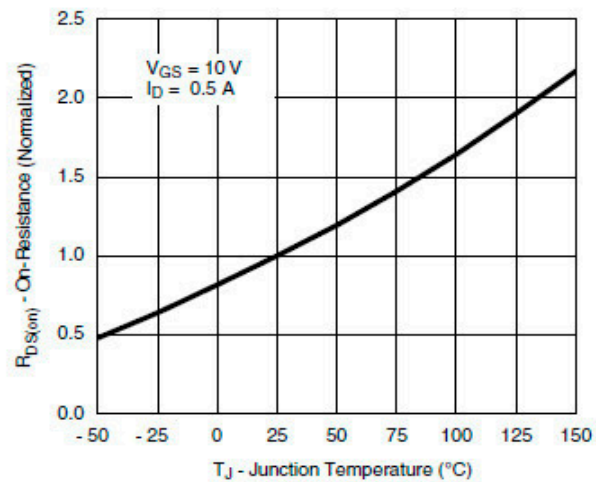
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge

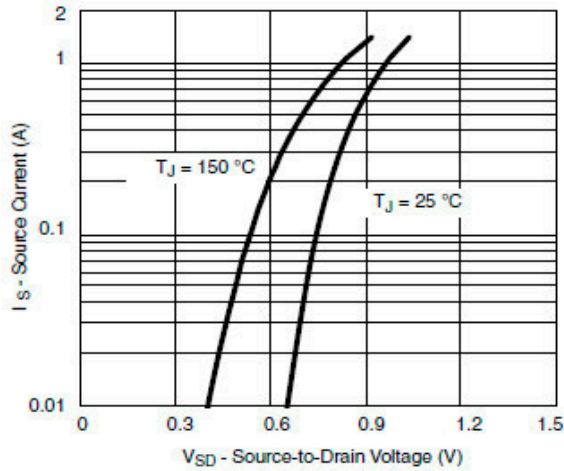


On-Resistance vs. Junction Temperature

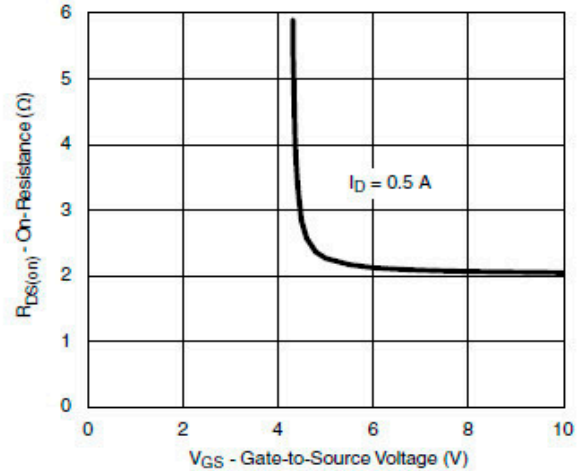
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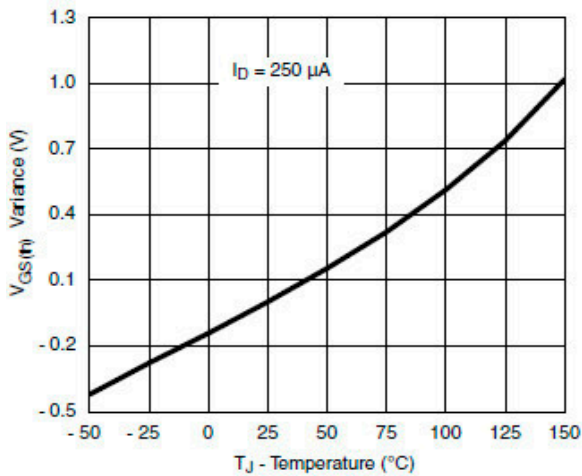
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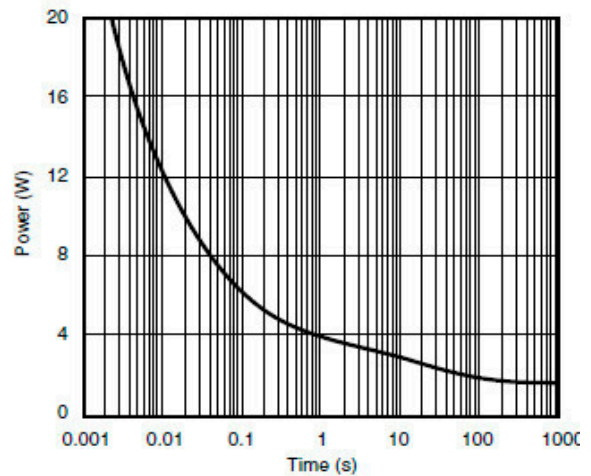
Source-Drain Diode Forward Voltage



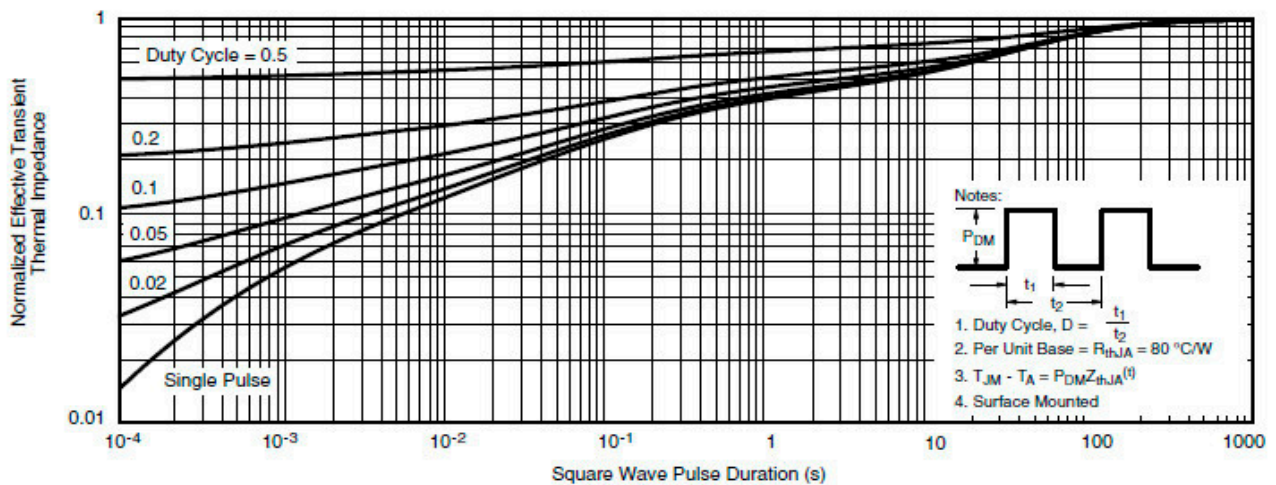
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

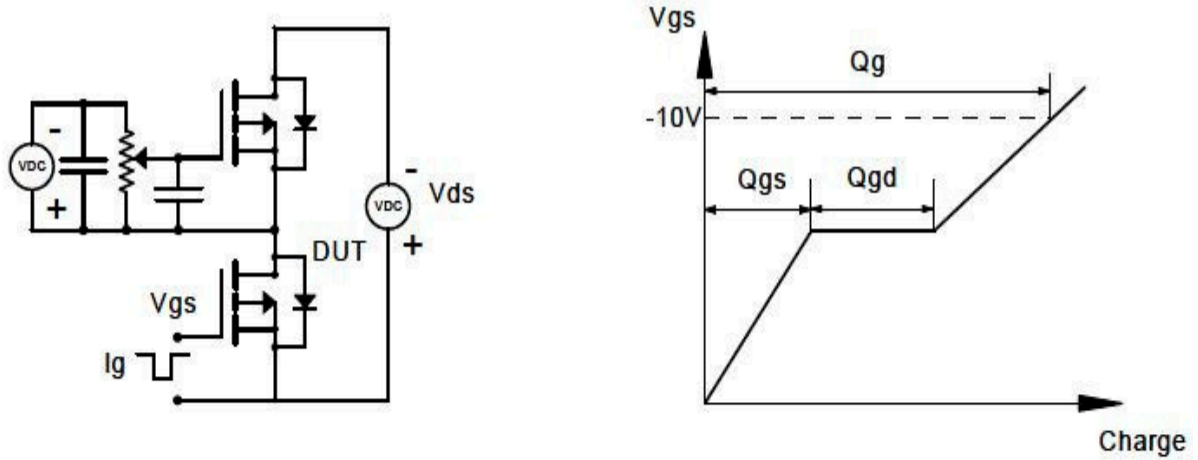
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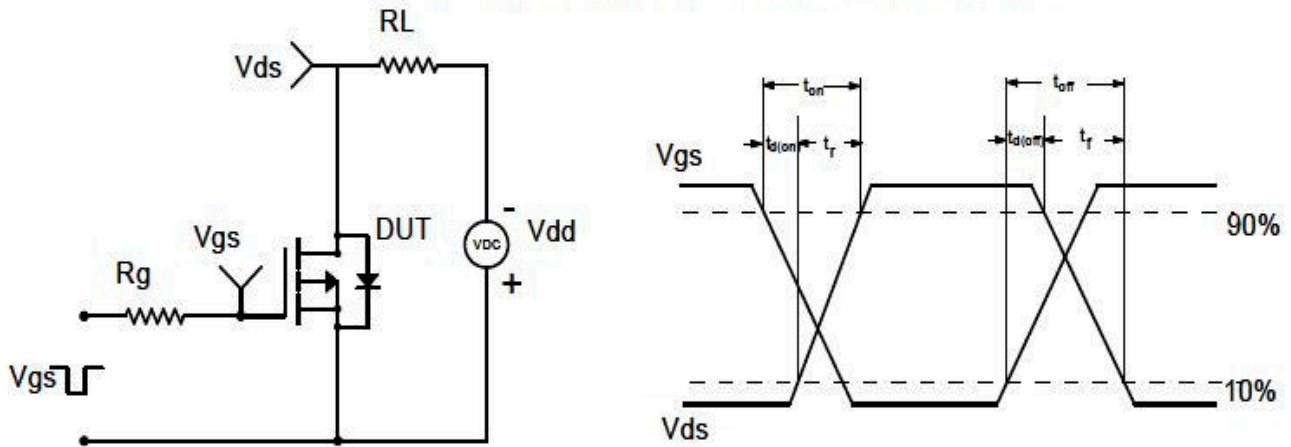
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■ 测试电路和波形

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

